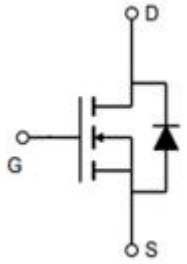
VSTF065R350NB

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
650V	35mΩ@10V	80A

Symbol



Symbol of VSTF065R350NB

Features

- Extremely low switching loss
- Excellent stability and uniformity
- RoHS and Halogen-Free Compliant
- Ultra-fast and robust body diode

Package Type

TO-247

Package Type of VSTF065R350NB

Application

- EV Charge
- LED lighting
- Telecom power
- Server power
- Solar/UPS

Ordering Information

Product Name	Package
VSTF065R350NB	TO-247

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current Note 1, T_C=25ºC	I_D	80	A
Pulsed Drain Current Note 2, T_C=25ºC	$I_{D,\ pulse}$	240	A
Continuous Diode Forward Current Note 1, T_C=25ºC	I_S	80	A
Diode Pulsed Current Note 2, T_C=25ºC	$I_{S,\ pulse}$	240	A
Max Power Dissipation Note 3, T_C=25ºC	P_D	831	W
Avalanche Current, Single Pulse Note 4	I_{AS}	9.1	A
Avalanche Energy, Single Pulse Note4	E_{AS}	3312	mJ
MOSFET dv/dt ruggedness, V_{DS}=0~480V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}=0~480V, I_{SD}<= I_D	dv/dt	50	V/ns
Operation and storage temperature	T_J,T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	0.158	-	ºC/W
Thermal Resistance, Junction-to-Ambient Note5	$R_{\theta JA}$	-	62	-	

Notes:

Note1: Calculated continuous current based on maximum allowable junction temperature.

Note2: Pulse width limited by safe operating area.

Note3: Based on max. junction temperature, using junction-case thermal resistance.

Note4: V_{DD}=100V,V_{GS}=10V, L=80mH, starting T_A=25 °C.

Note5: When mounted on 1 inch square copper board, t≤10sec. The value in any given application depends on the user's specific board design.

Electrical Characteristics(T_A= 25 ºC, unless otherwise specified)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250uA	650	-	-	V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V	-	-	10	uA
Gate-Source Leakage Current	Forward	I_{GSSF}	V_{GS}=30V, V_{DS}=0V	-	-	100	nA
	Reverse	I_{GSSR}	V_{GS}=-30V, V_{DS}=0V	-	-	-100	
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250uA	2	3.0	4	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=40A	-	28	35	mΩ
Gate Resistance		R_G	F=1MHz, Open Drain	-	0.5	-	Ω
Dynamic Characteristics							
Input Capacitance		C_{iss}	V_{DS}=50V	-	8278	-	pF
Output Capacitance		C_{oss}	V_{GS}=0V	-	351.8	-	pF
Reverse Transfer Capacitance		C_{rss}	f=100kHz	-	6.05	-	pF
Effective output capacitance, energy related		$Co_{(er)}$	V_{GS}=0 V,	-	305.9	-	pF
Effective output capacitance, time related		$Co_{(tr)}$	V_{DS}=0 V-400 V	-	968.1	-	pF
Turn-on Delay Time		$t_{d(on)}$	V_{DS}=400V	-	116.5	-	ns
Rise Time		t_r	I_D=30A	-	38	-	
Turn-off Delay Time		$t_{d(off)}$	R_G=25Ω	-	289	-	
Fall Time		t_f	V_{GS}=10V	-	16.7	-	
Gate Charge Characteristics							
Gate to Source Charge		Q_{gs}	V_{DS}=400V	-	21.6	-	nC
Gate to Drain Charge		Q_{gd}	I_D=30A	-	56.3	-	
Gate Charge Total		Q_g	V_{GS}=0 to 10V	-	134	-	
Gate Plateau Voltage		$V_{Plateau}$		-	3.7	-	V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_S=80A	-	1.0	1.4	V
Reverse Recovery Time		t_{rr}	V_R=400V	-	153	-	ns
Reverse Recovery Charge		Q_{rr}	I_S=30A	-	1.1	-	uC
Peak Reverse Recovery Current		I_{rrm}	di/dt=100A/us	-	13	-	A

Electrical Characteristics Diagrams

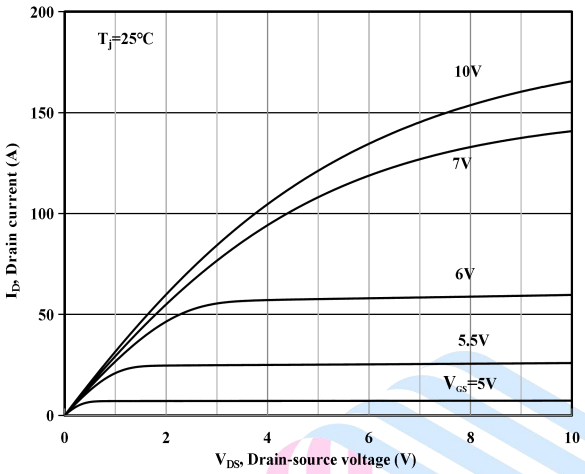


Figure 1. Typ. output characteristics

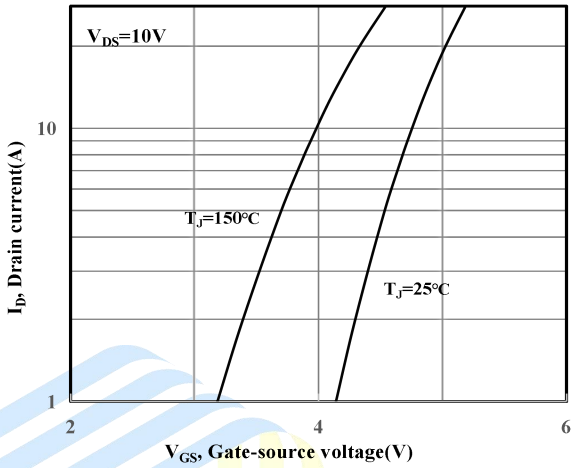


Figure 2. Typ. transfer characteristics

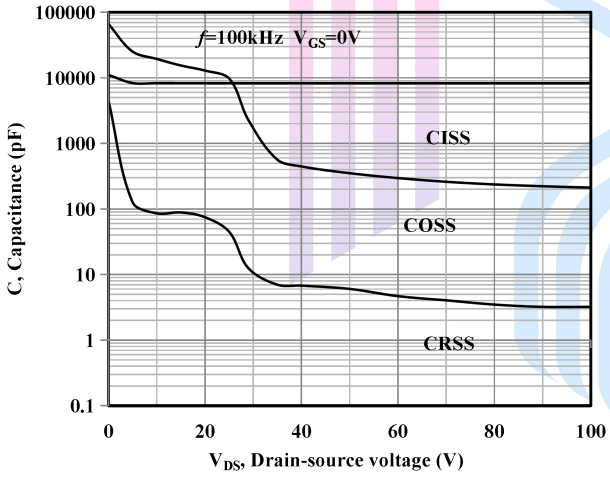


Figure 3. Typ. Capacitances

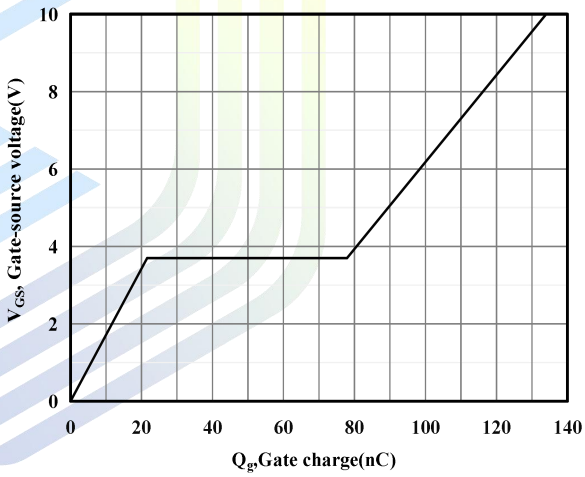


Figure 4. Typ. gate charge

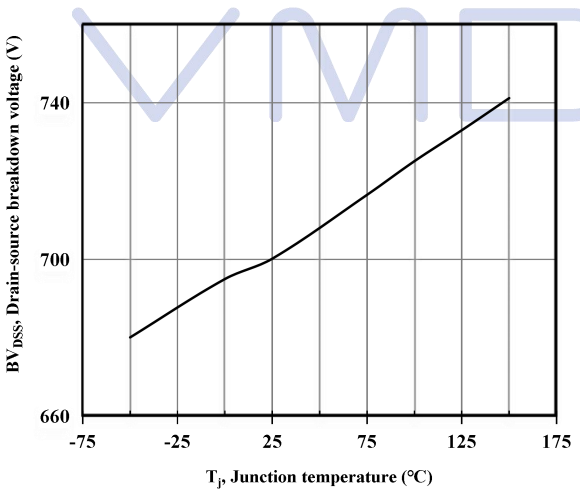


Figure 5. Drain-source breakdown voltage

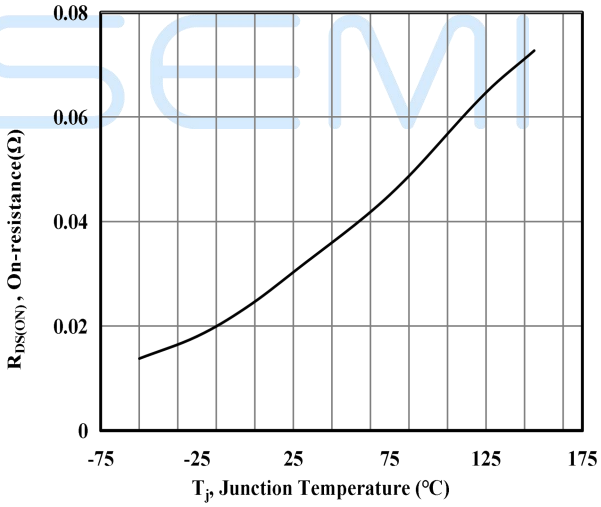


Figure 6. Drain-source on-state resistance

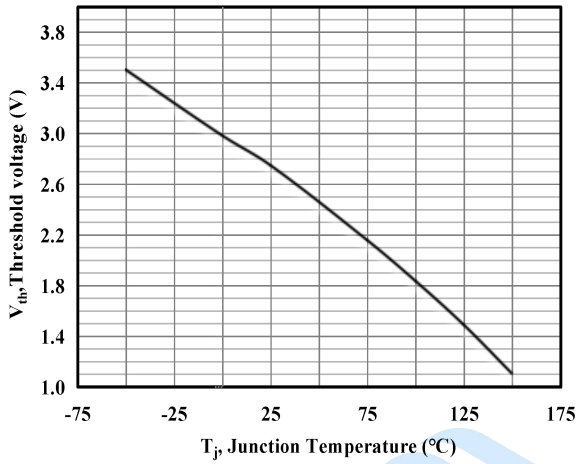


Figure 7. Threshold voltage

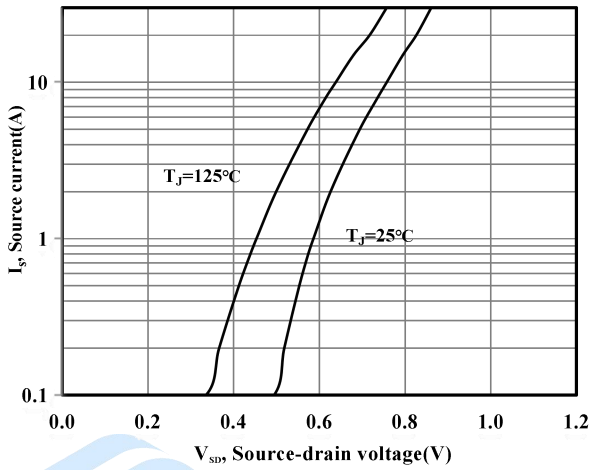


Figure 8. Forward characteristic of body diode

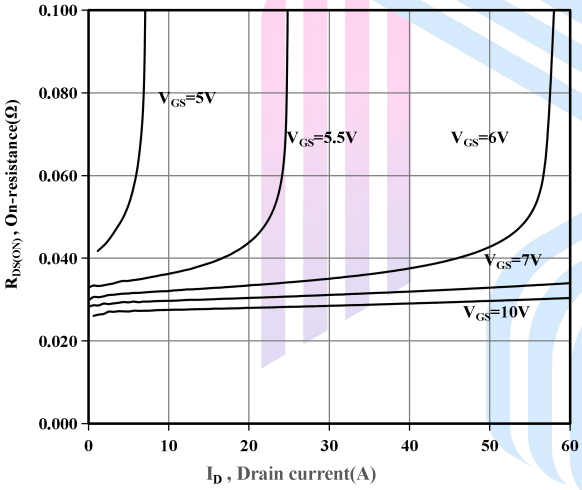


Figure 9. Drain-source on-state resistance

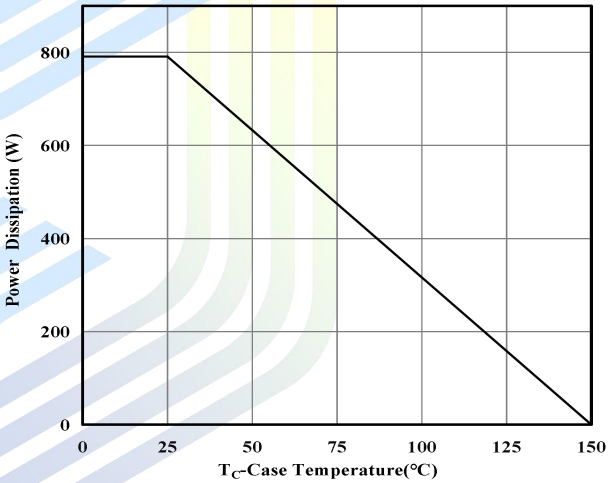


Figure 10. Power Dissipation

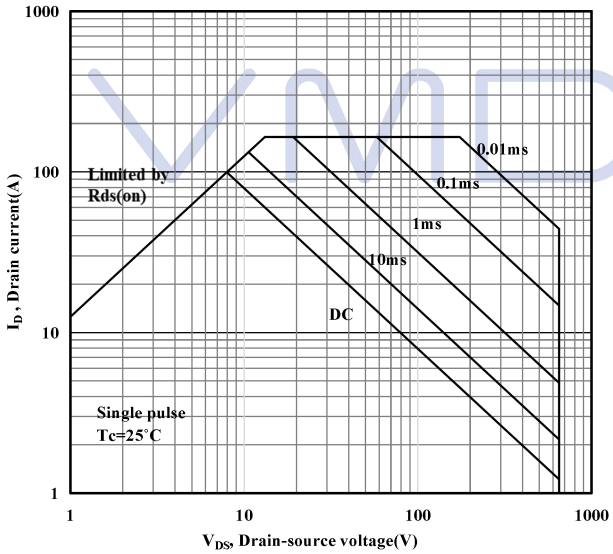


Figure 11. Safe operation area T_C=25℃

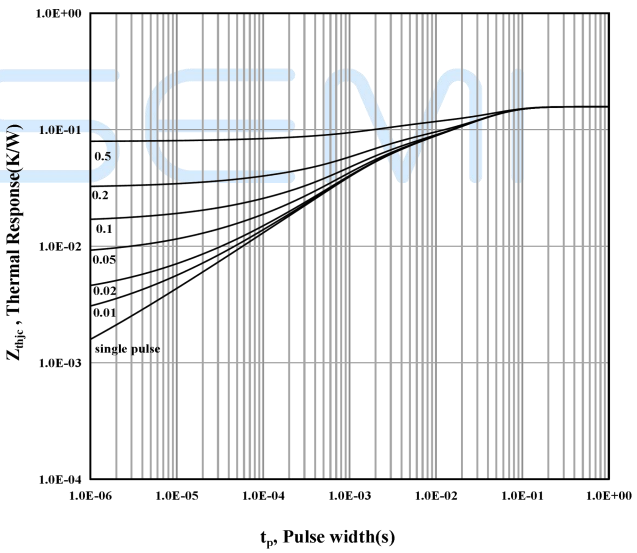
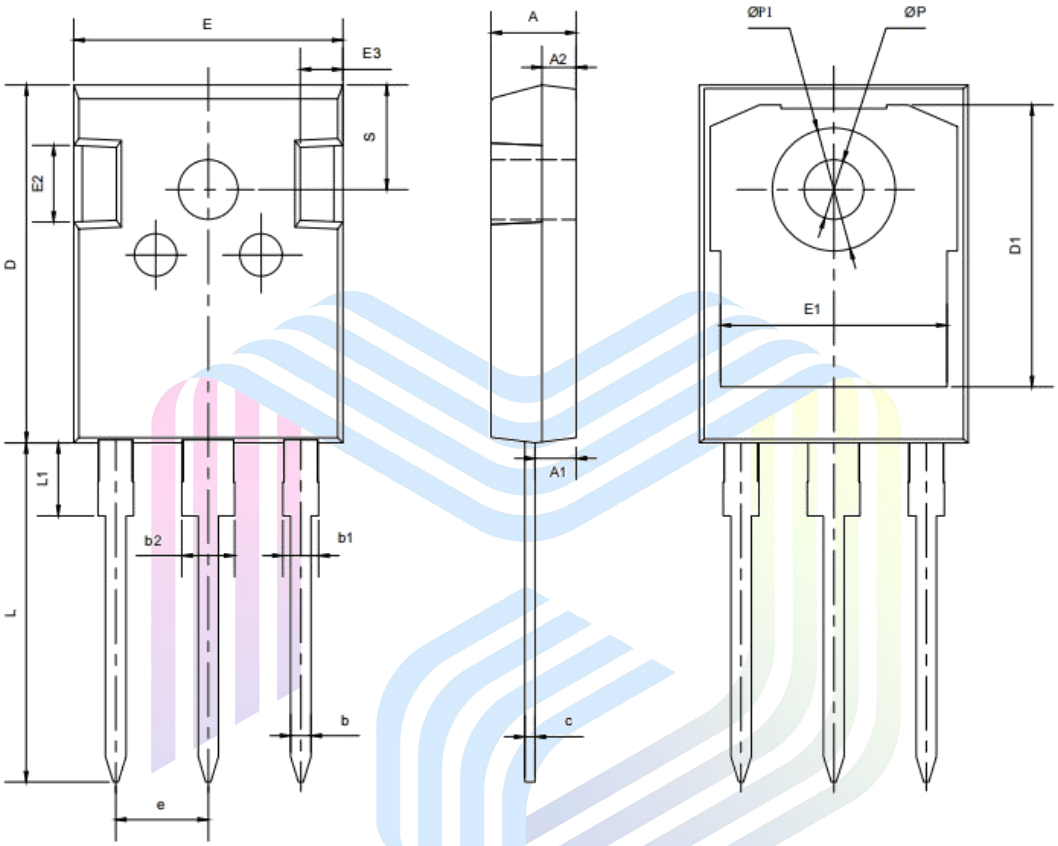


Figure 12. Max. transient thermal impedance

Mechanical Dimensions

TO-247F Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	MAX
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b1	1.91	2.21
b2	2.91	3.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.60
E3	2.10	2.70
e	5.44BSC	
L	19.62	20.22
L1	-	4.30
φP	3.40	3.80
φP1	-	7.30
S	6.15BSC	

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